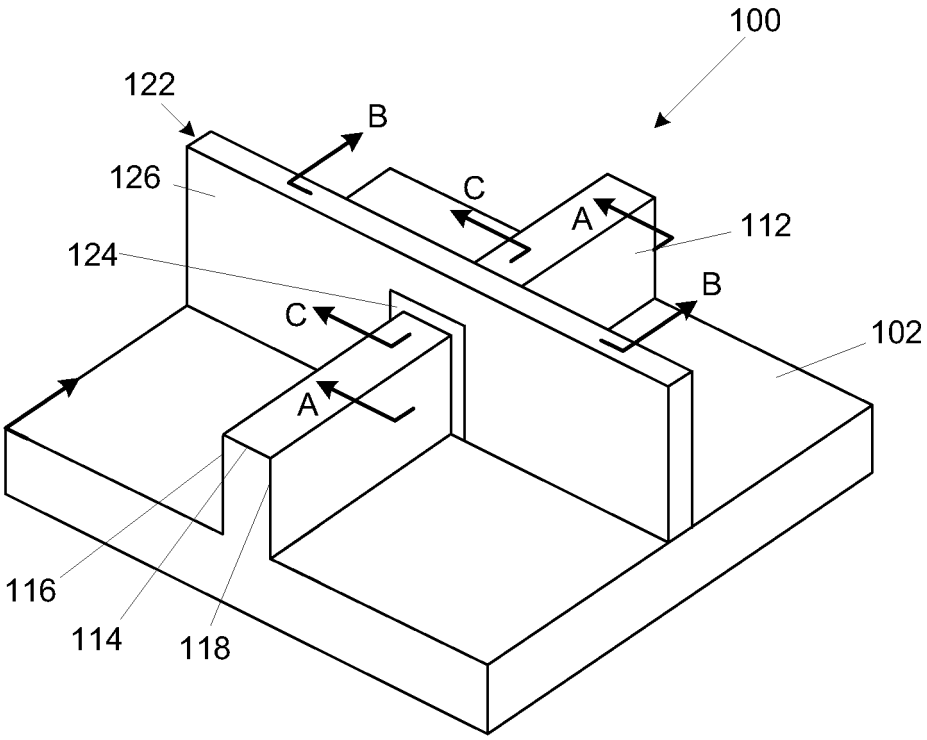


FIG. 1

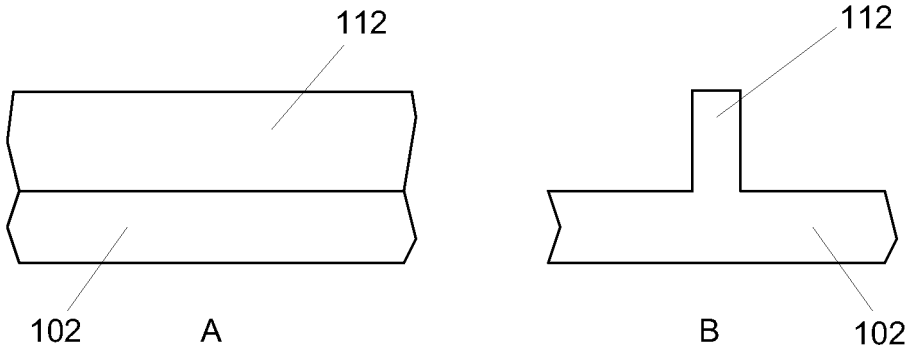


FIG. 2

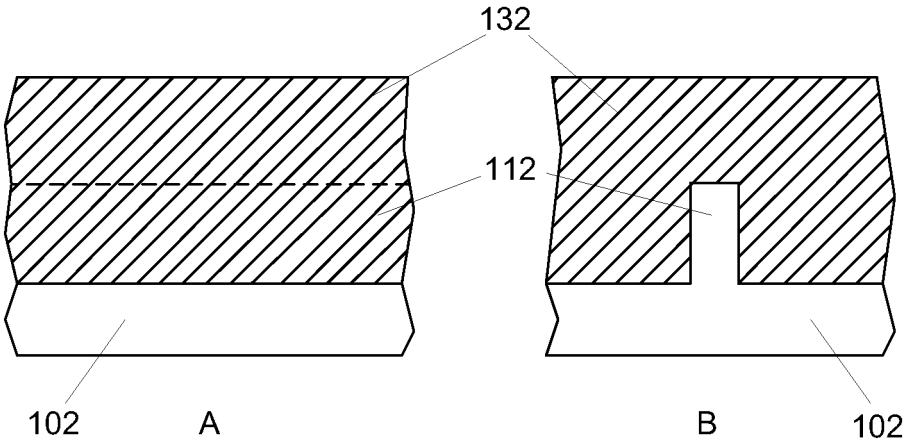


FIG. 3

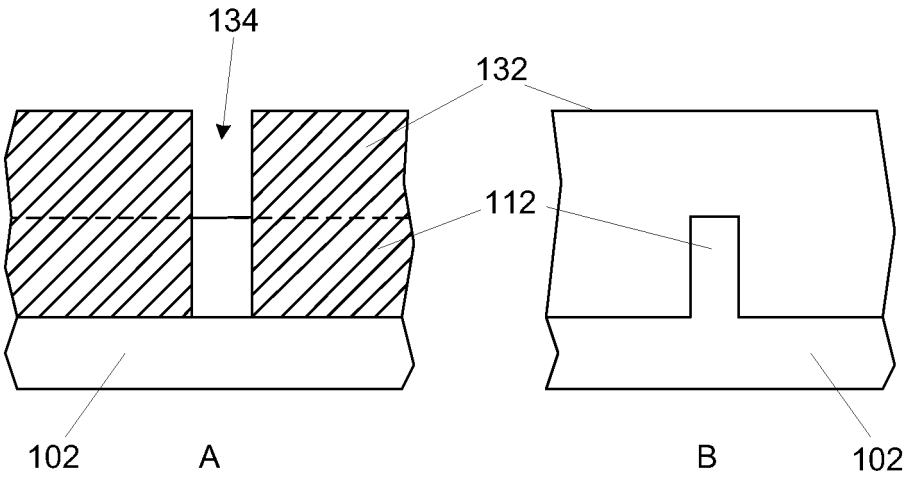


FIG. 4

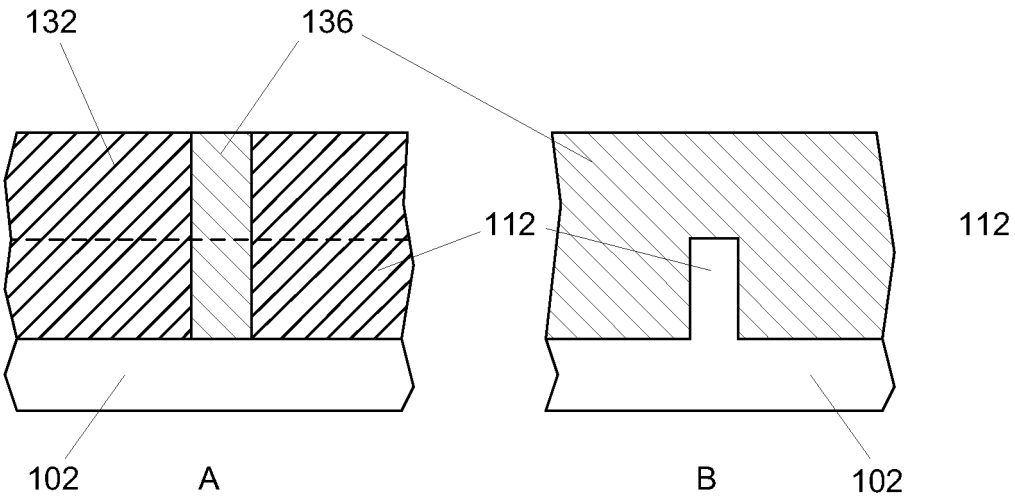


FIG. 5

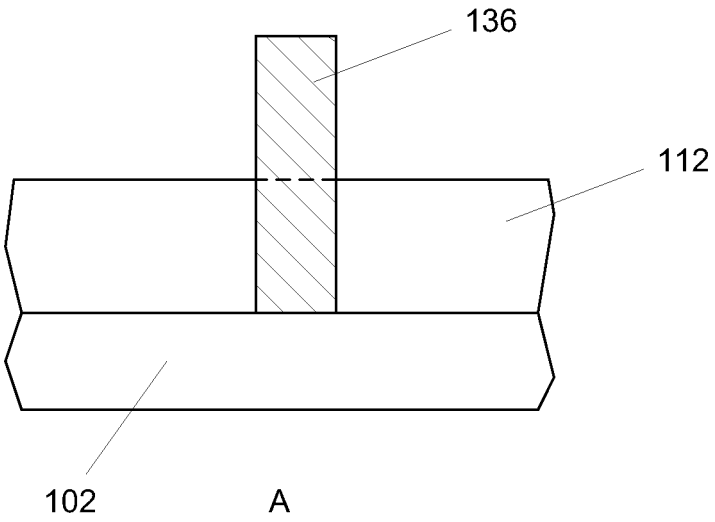


FIG. 6

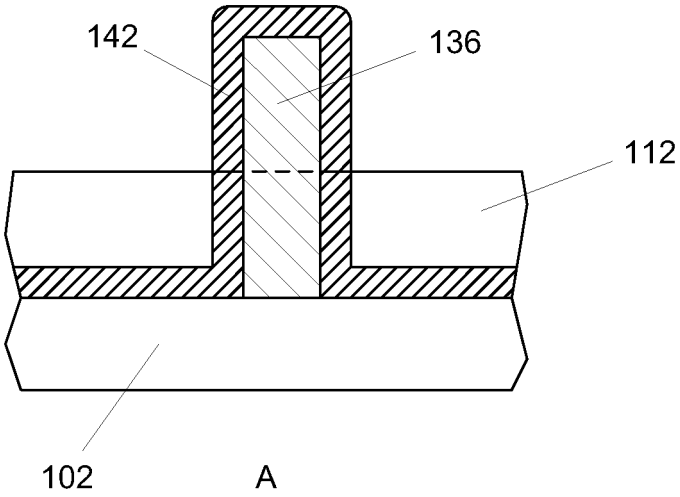


FIG. 7

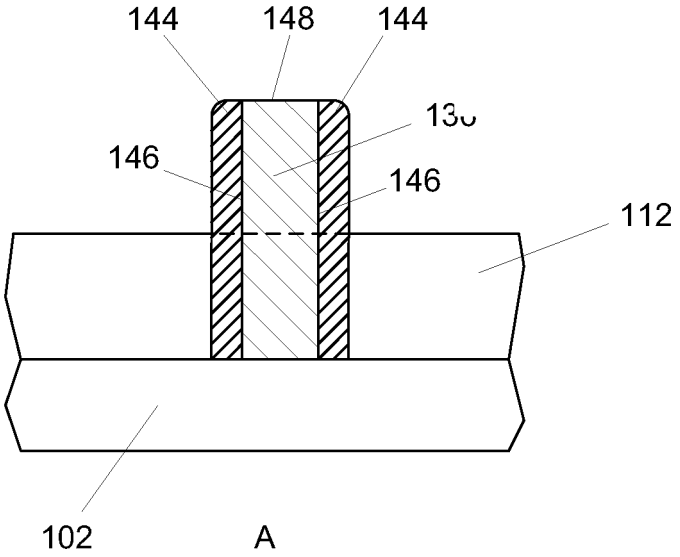


FIG. 8

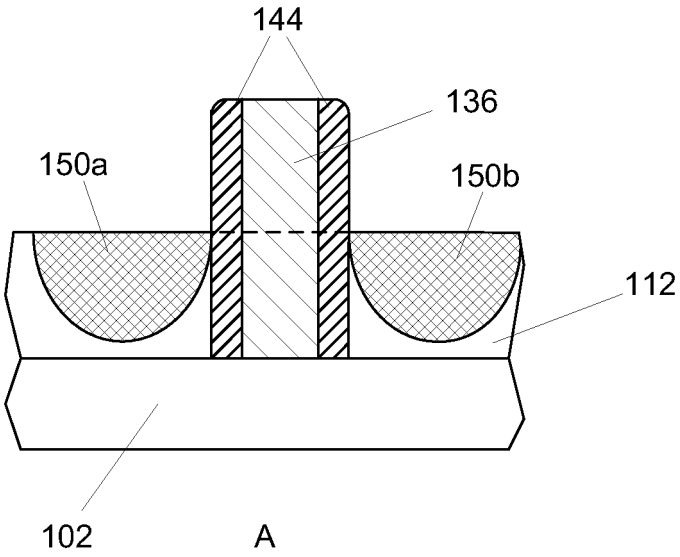


FIG. 9

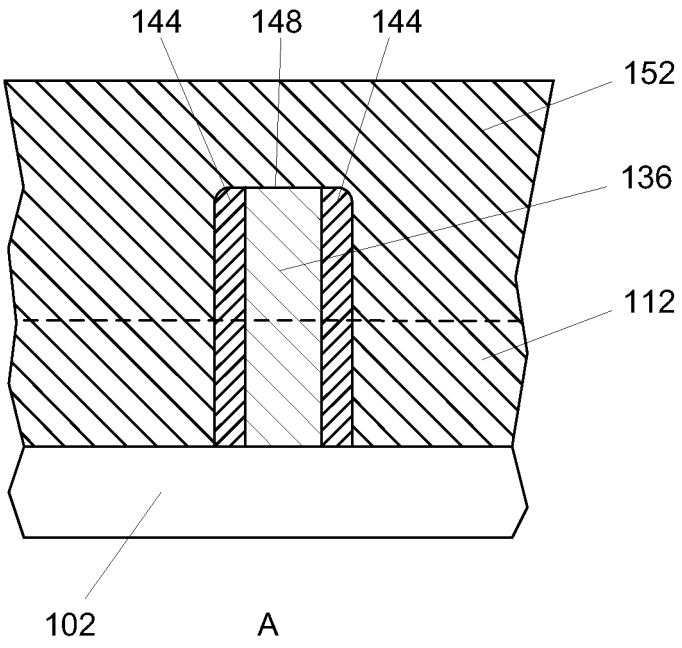


FIG. 10

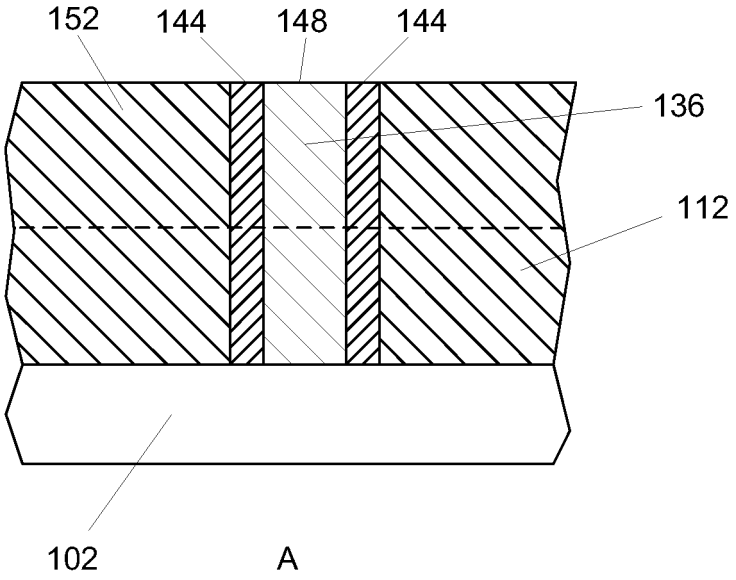


FIG. 11

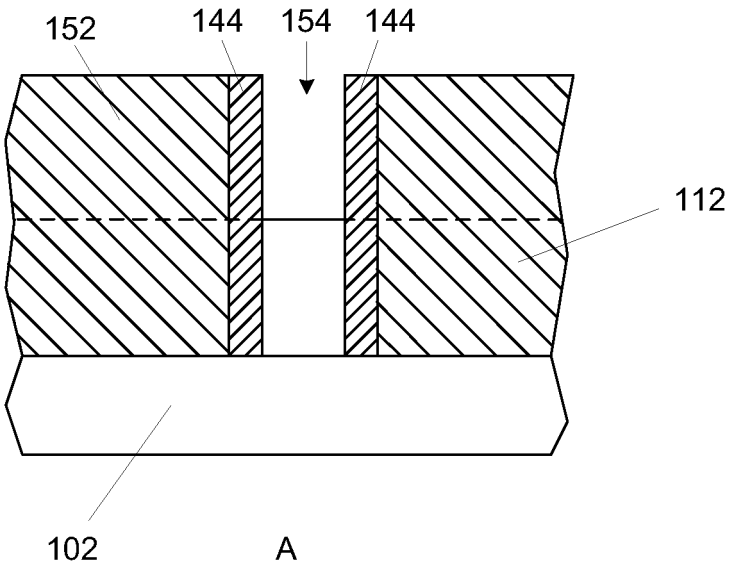


FIG. 12

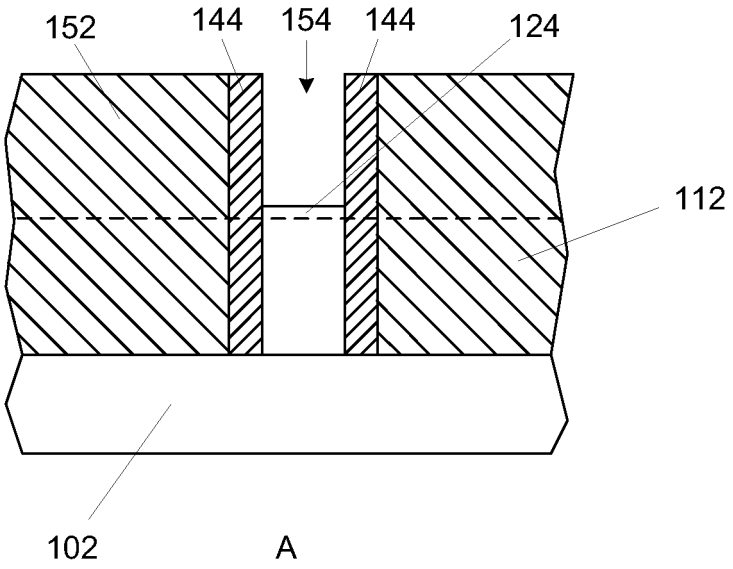


FIG. 13

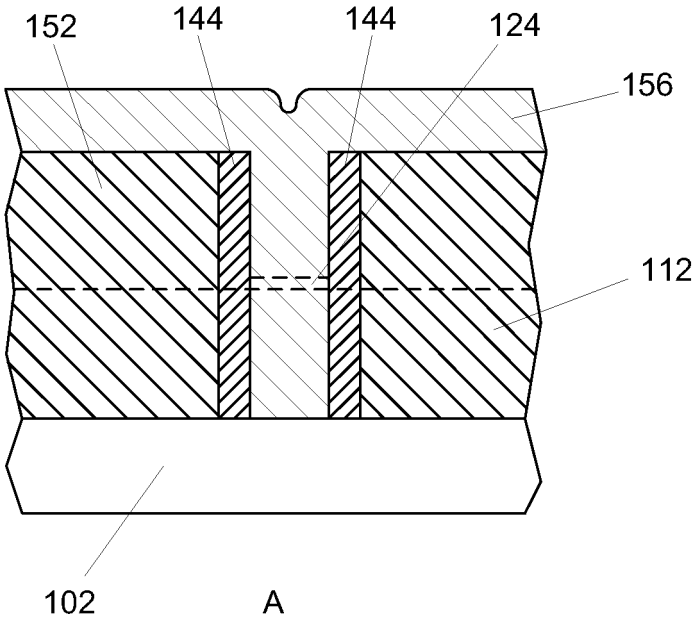


FIG. 14

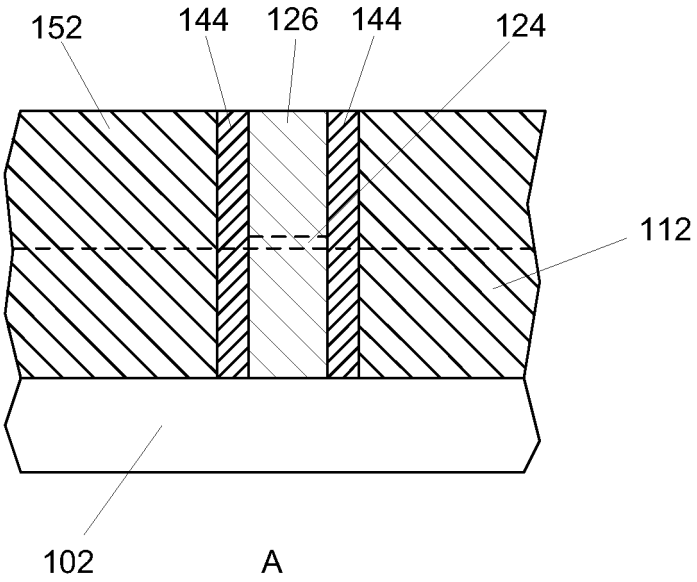

152
144
126
144
124
112
102
A

FIG. 15

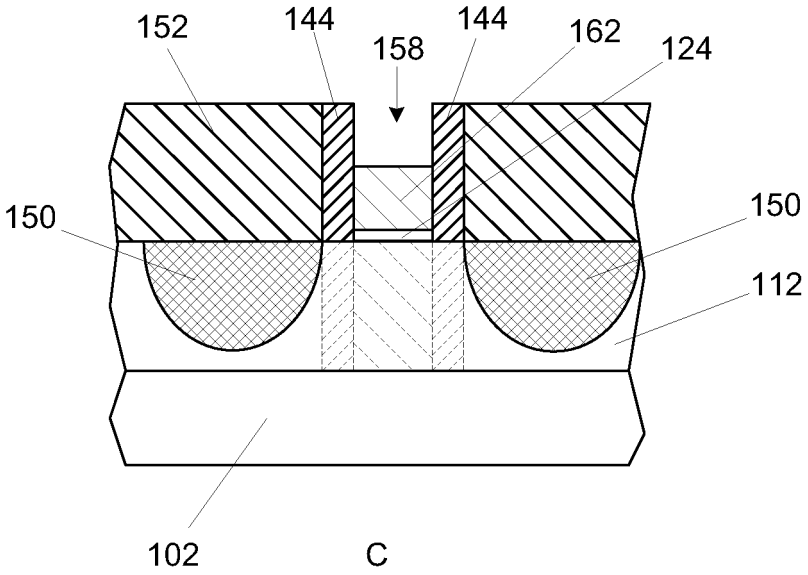

152
144
158
144
162
124
150
150
112
102
C

FIG. 16

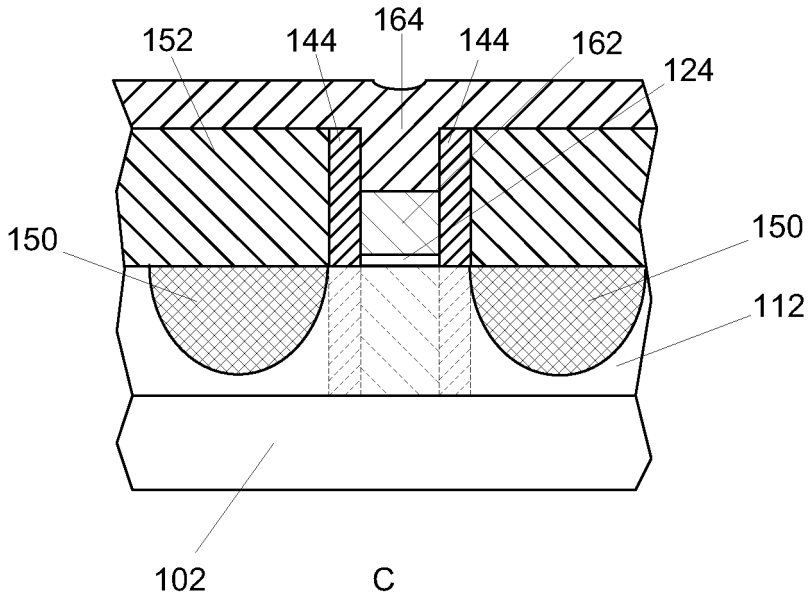

164
152
144
144
162
124
150
150
112
102
C

FIG. 17

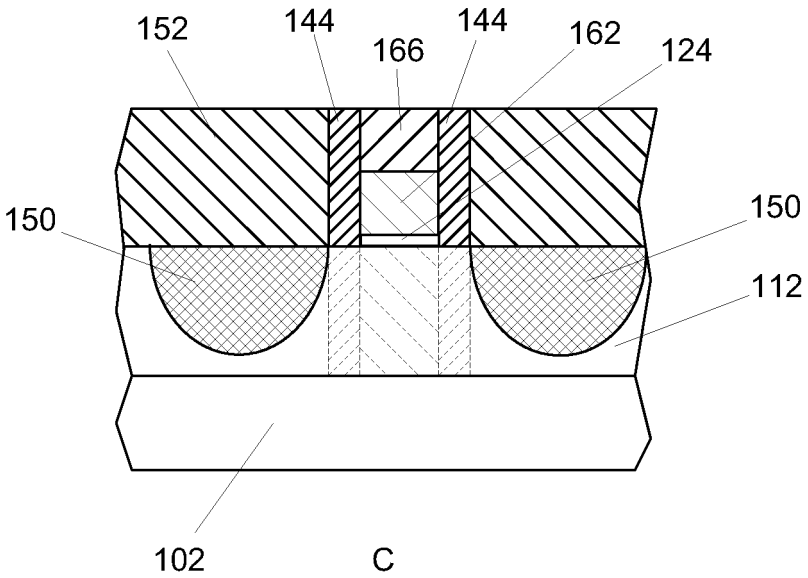

152
144
166
144
162
124
150
150
112
102
C

FIG. 19

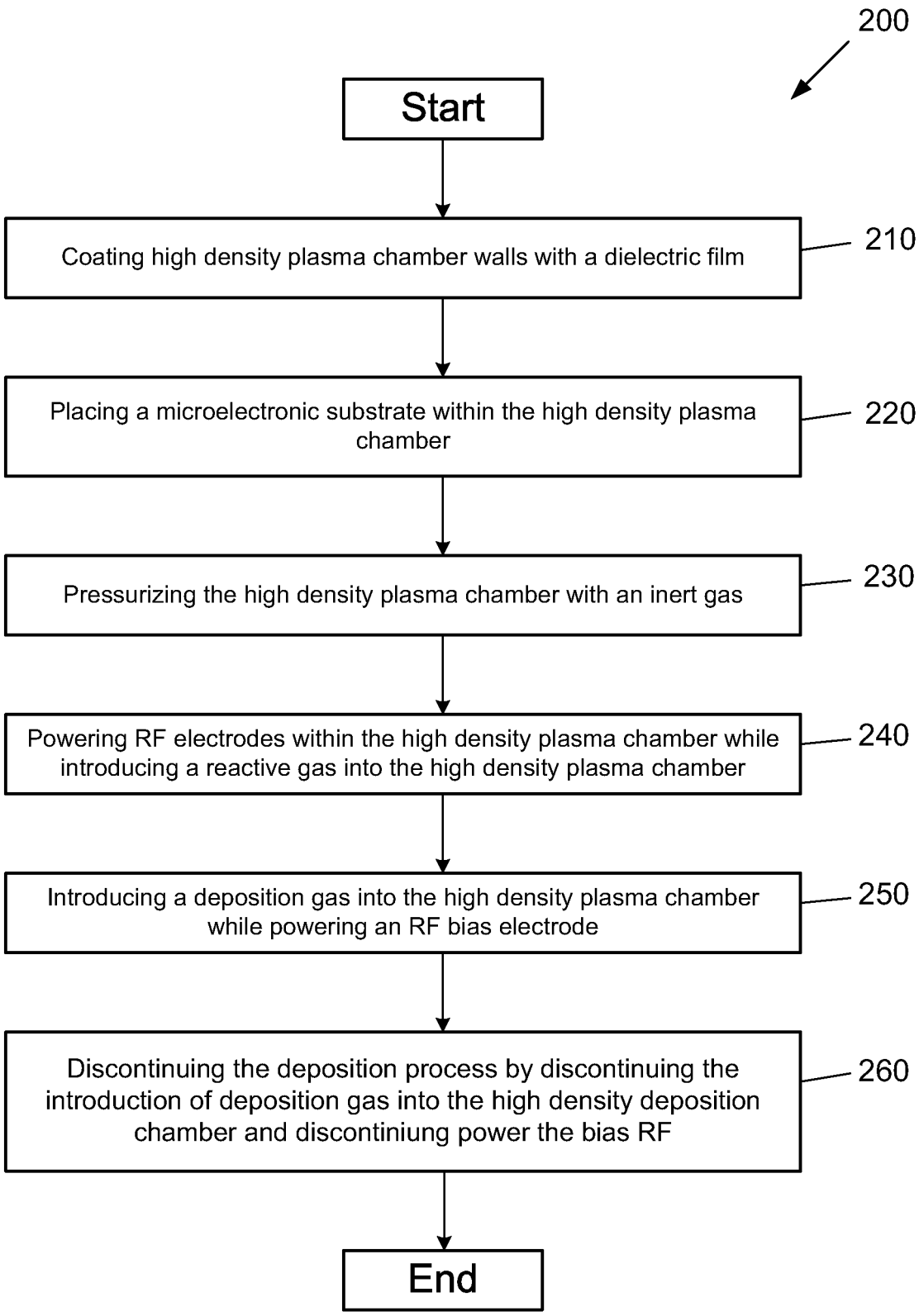

200
Start
Coating high density plasma chamber walls with a dielectric film
210
Placing a microelectronic substrate within the high density plasma chamber
220
Pressurizing the high density plasma chamber with an inert gas
230
Powering RF electrodes within the high density plasma chamber while introducing a reactive gas into the high density plasma chamber
240
Introducing a deposition gas into the high density plasma chamber while powering an RF bias electrode
250
Discontinuing the deposition process by discontinuing the introduction of deposition gas into the high density deposition chamber and discontiniung power the bias RF
260
End

FIG. 18

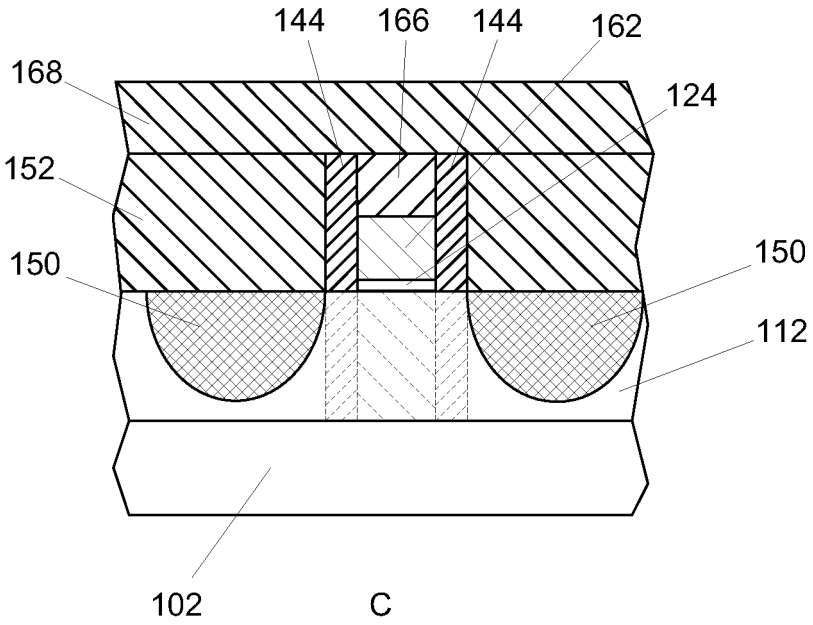

144
166
144
162
168
124
152
150
150
112
102
C

FIG. 20

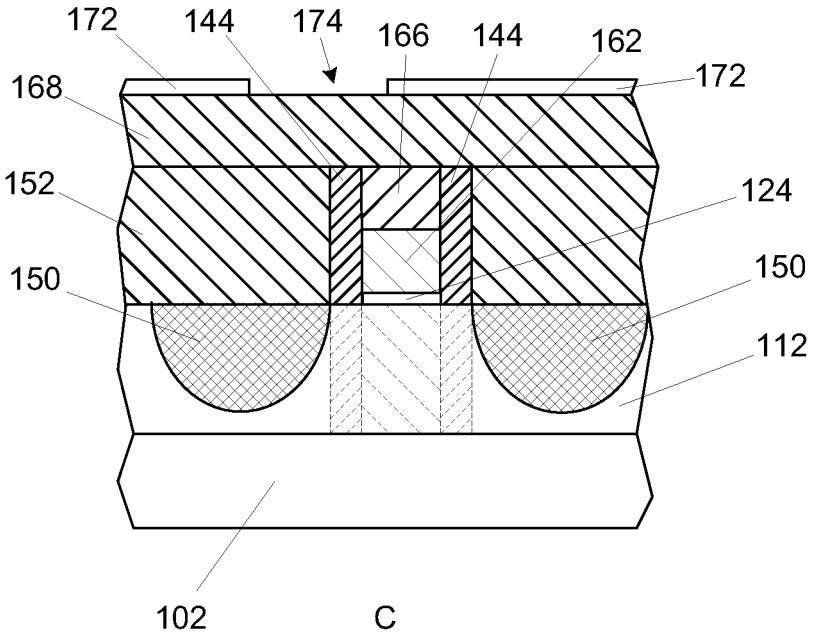

172
144
174
166
144
162
168
172
152
124
150
150
112
102
C

FIG. 21

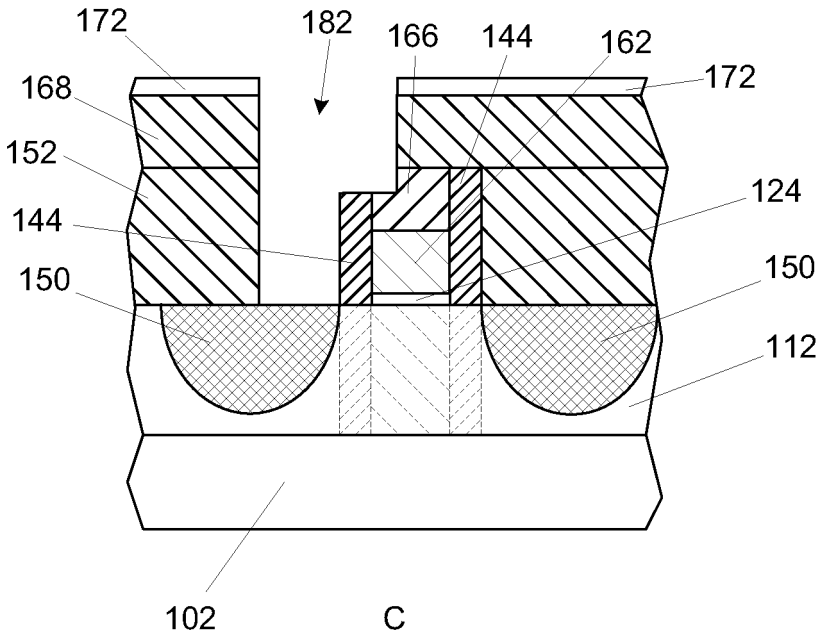

172
182
166
144
162
172
168
152
124
144
150
150
112
102
C

FIG. 22

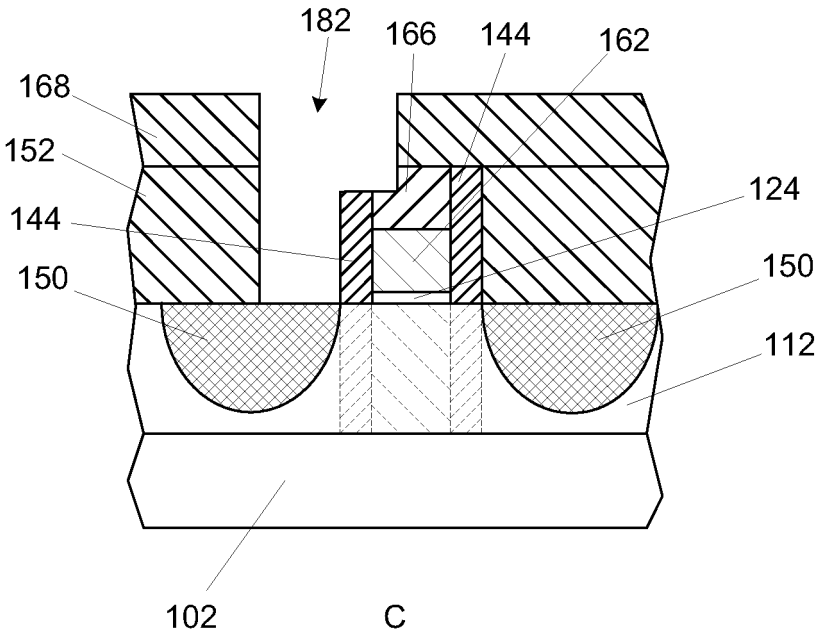

182
166
144
162
168
152
124
144
150
150
112
102
C

FIG. 23

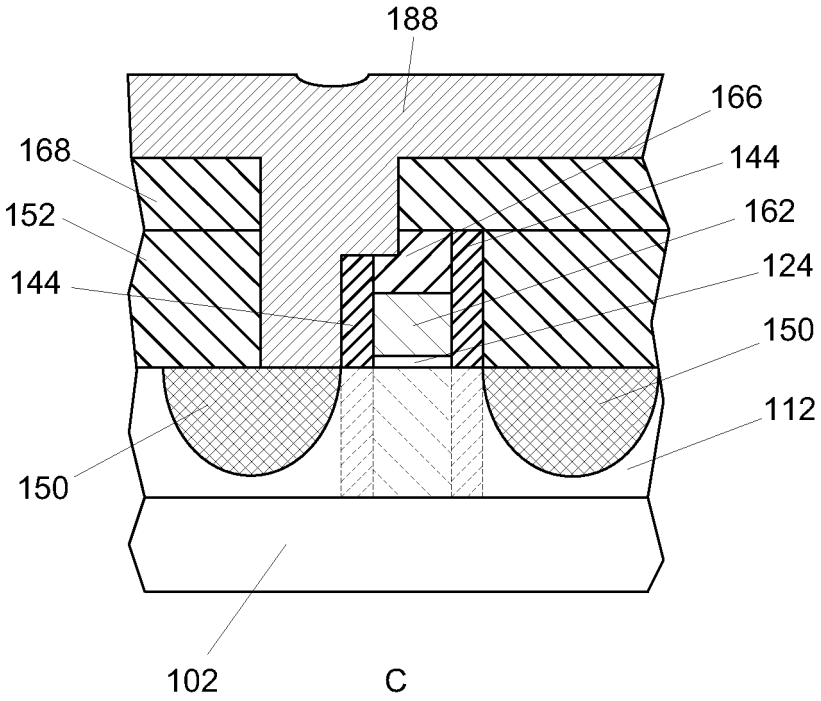

188
166
168
144
152
162
144
124
150
112
150
102
C

FIG. 24

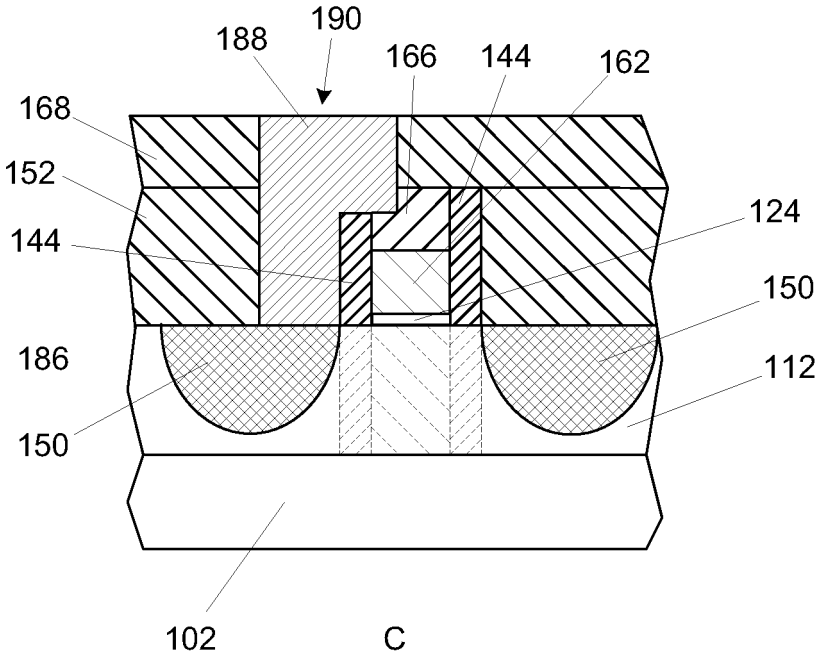

190
188
166
144
162
168
152
124
144
150
186
112
150
102
C

FIG. 25